

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	647215	(semiconductor si silicon gaas) with (substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:00
L2	26095	(barrier intervent intervented intervention intervented) with (tin ti tisin ((silicon titanium) adj4 nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:03
L3	1954628	(buried conduct conductive conducting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:03
L4	73183	3 with (tin ti tisin ((silicon titanium) adj4 nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:03
L5	6488	1 and 2 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:04
L6	5589	(opening plug via) and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:04
L7	4948	(transistor gate source drain) and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:06
L8	3162	(contact with (hole plug)) and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:07

L9	1231	(interconnect onterconnection) and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 01:07
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